



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Nevin et al. GROUP: 2823
SERIAL NO: 10/699,503 EXAMINER: L.H. Ming
FILED: October 31, 2003
FOR: METHOD FOR FORMING A FILLED TRENCH IN A
SEMICONDUCTOR LAYER OF A SEMICONDUCTOR
SUBSTRATE, AND A SEMICONDUCTOR SUBSTRATE WITH A
SEMICONDUCTOR LAYER HAVING A FILLED TRENCH
THEREIN

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Sir:

**SUPPLEMENTAL RESPONSE TO THE NOTICE OF DRAWING
INCONSISTENCY MAILED
MAY 25, 2006**

In response to the Notice of Drawing Inconsistency mailed May 25, 2006, and supplemental to the Response mailed June 19, 2006, Applicants submit herewith a clean copy of substitute sheet 10 of the specification.

If any further information or amendments are needed to proceed with the issuance of this case, please contact the Applicant's undersigned representative immediately.

Respectfully submitted,


Matthew E. Connors
Registration No. 33,298
Gauthier & Connors LLP
225 Franklin Street, Suite 2300
Boston, Massachusetts 02110
Telephone: (617) 426-9180 Ext. 112



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SUBSTITUTE SHEET

Fig. 5 is a view similar to Fig. 4 of an SOI structure according to another embodiment of the invention,

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Fig. 6 is a view similar to Fig. 4 of an SOI structure according to a further embodiment of the invention being formed,

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Fig. 7 is a view similar to Fig. 4 of the SOI structure of Fig. 6 also being formed,

Fig. 8 is a view similar to Fig. 4 of an SOI structure according to a still further embodiment of the invention,

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Fig. 9 is a view similar to Fig. 4 of an SOI structure according to a still further embodiment of the invention,

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Fig. 10 is a view similar to Fig. 4 of an SOI structure according to the invention, which is substantially similar to the SOI structure of Figs. 3 and 4 being formed,

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Fig. 11 is a view similar to Fig. 4 of the SOI structure of Figs. 6 and 7 being formed,

Fig. 12 is a view similar to Fig. 4 of the SOI structure of Figs. 6 and 7 also being formed,

Fig. 13 is a view similar to Fig. 4 of the SOI structure of Fig. 9 being formed, and

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Figs. 14 to 20 are photomicrographs of semiconductor layers with isolation filled trenches whereby the isolation filled trenches have been formed by methods according to the invention.